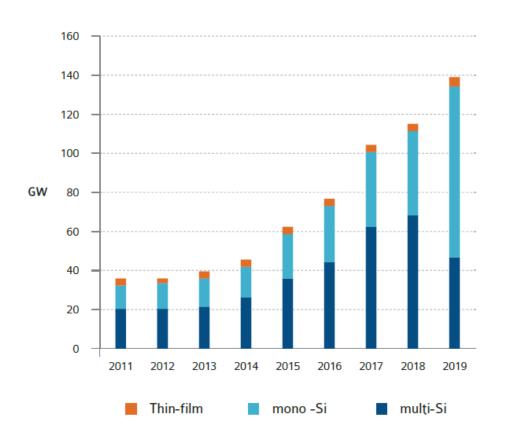


#### **PV TECHNOLOGIES**

- Is there a c-Si technology?
- Feedstock
- Wafer
- Cells
- Module
- Other silicon concepts
- Materials availability

**FIGURE 4.6:** PV MODULE PRODUCTION PER TECHNOLOGY IN 2019

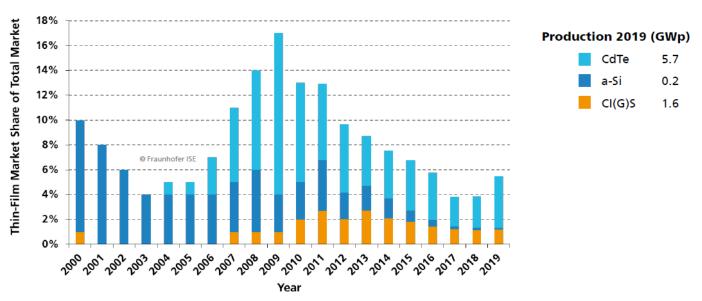


Silicon is the dominant technology

High efficiency is gaining market share

**Market Share of Thin-Film Technologies** 

Percentage of Total Global PV Production



Data: from 2000 to 2009: Navigant; from 2010: IHS Markit. Graph: PSE Projects GmbH 2020

Thin films were popular when polysilicon was expensive

Amorphous silicon is disappearing

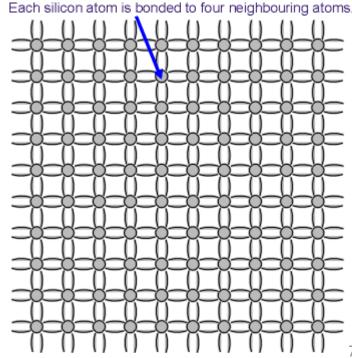


**Siemens Multicrystalline** Screenprint, Wire saw **BSF, SiN** casting process Crystal **Silicon** Wafering Cell growth purification Semi-grade Si Multi Si Selectivemitter, Union Bridgeman, RTP, optical Carbide, FBR confinement... **EM** casting Solar-grade Si **Metallization** Mono Si FBR (HSiCI3), Inkjet, PL, CZ, 3-crystal UMGS, VLD evaporation Silicon ribbons Other concepts EFG, String Ribbon, RGS, HIT, buried or DWeb, RST, SWeb, EZ, SDS, S'tile point contact... **Spherical** Sliver **Crystalline silicon thin films** Epitaxial growth or multicrystalline growth (annealing,

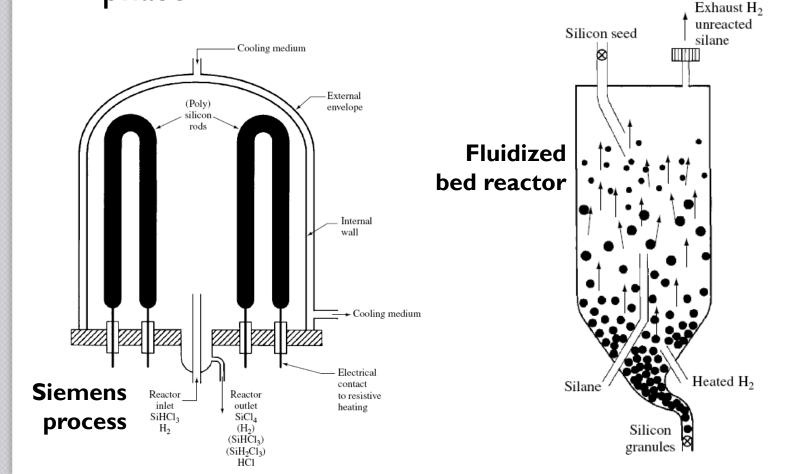
Silicon nanoparticles (Innovalight)

metal induced, laser induced or zone melting recrystallization)

Silicon is the second most abundant element on Earth after oxygen (28% of the Earth's crust). Its most familiar forms are sand and quartzite (the latter one is more pure).



Feedstock: obtaining hyperpure silicon from gas phase





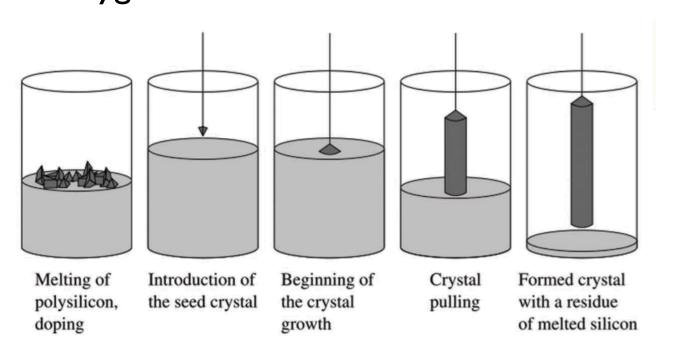
Feedstock: obtaining hyperpure silicon from gas phase



#### Crystalline silicon may be used in PV in different forms:

Descriptor	Symbol	Grain Size	Common Growth Techniques
Single crystal	sc-Si	>10cm	Czochralski (CZ) float zone (FZ)
Multicrystalline	mc-Si	Imm-I0cm	Cast, sheet, ribbon
Polycrystalline	pc-Si	l µm-l mm	Chemical-vapour deposition
Microcrystalline	μc-Si	<iµm< td=""><td>Plasma deposition</td></iµm<>	Plasma deposition

Czochralski silicon is the standard for electronics industry. High quality (mono) with contamination with oxygen and carbon into the melt.

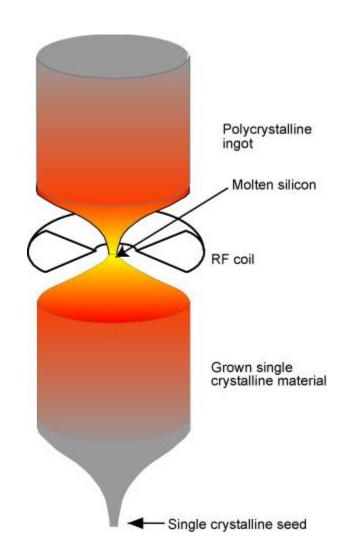




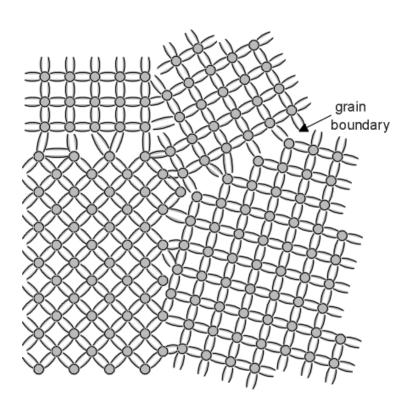
Float zone silicon is the best quality silicon

No contamination but very expensive. Only for very demanding applications.

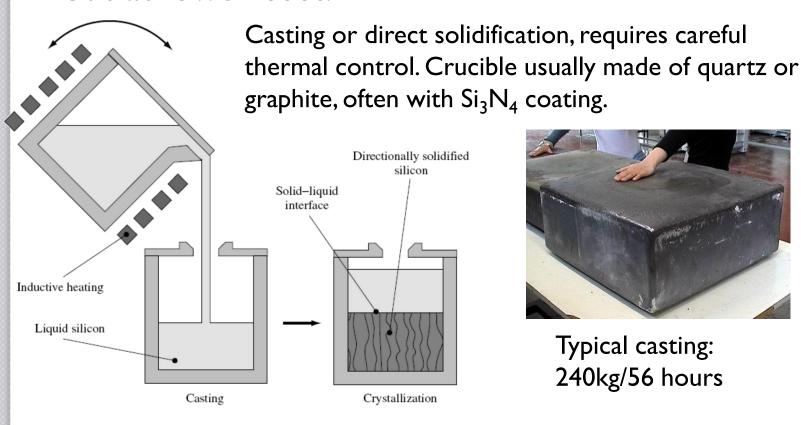




Multicrystalline silicon offers acceptable quality but at lower cost



Multicrystalline silicon offers acceptable quality but at lower cost.





Typical casting: 240kg/56 hours

Multicrystalline ingots require sawing.

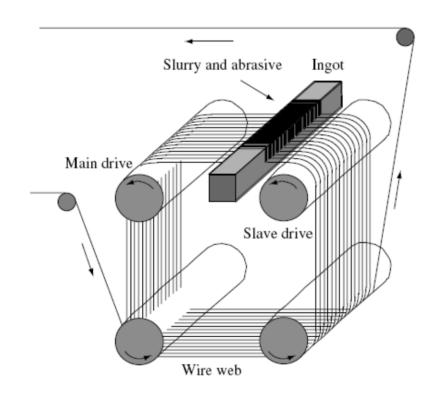
Kerf loss and saw damage removal is significant (and

costly).



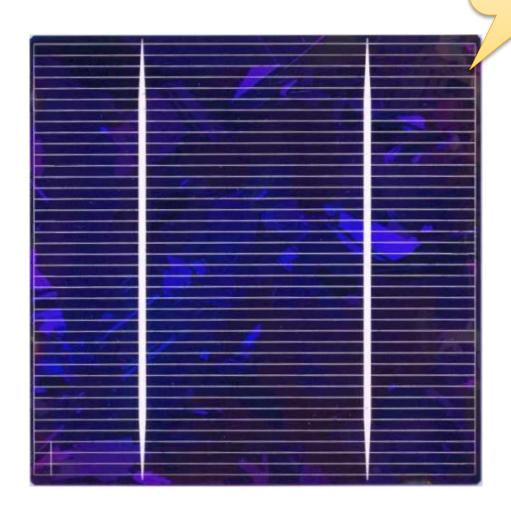








Check:
PVCDROM
Chapter 6





- Saw damage etch
- Phosphorous diffusion
- Edge isolation
- Back contact print
- Firing
- Anti reflective coating
- Front contact print
- Firing
- Testing & sorting

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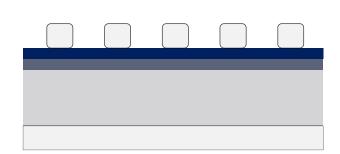
- Saw damage etch
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- Saw damage etch
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- Front contact print
- Firing
- Testing & sorting



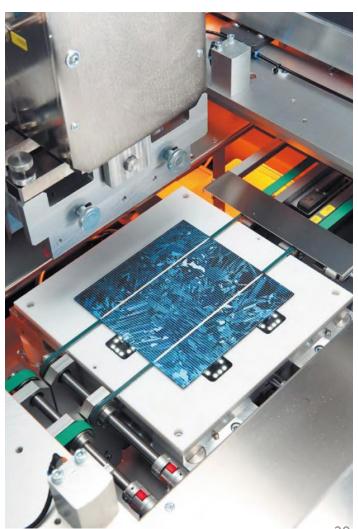
Phosphorous diffusion can be inline continuous or batch type P source: POCI<sub>3</sub>





Screenprinting using silver paste is standard.

Inkjet alternatives and/or other materials are fashionable research topics.



Handling thin wafers and keeping high yields may be challenging

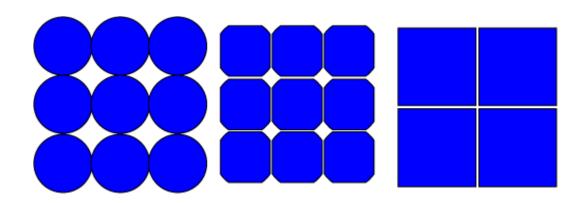






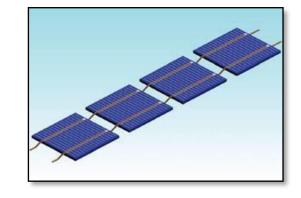
#### PV silicon module

- Packing density
- Interconnection PV cells
- Encapsulation

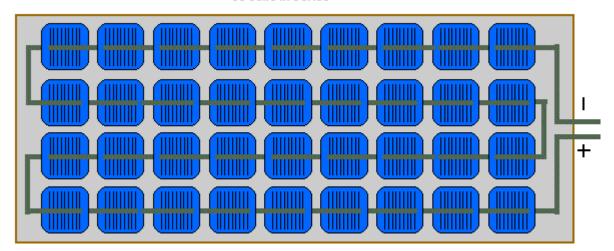


#### PV silicon module

- Packing density
- Interconnection PV cells
- Encapsulation

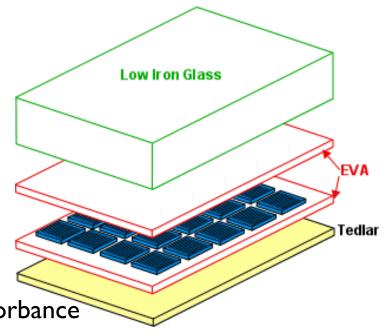


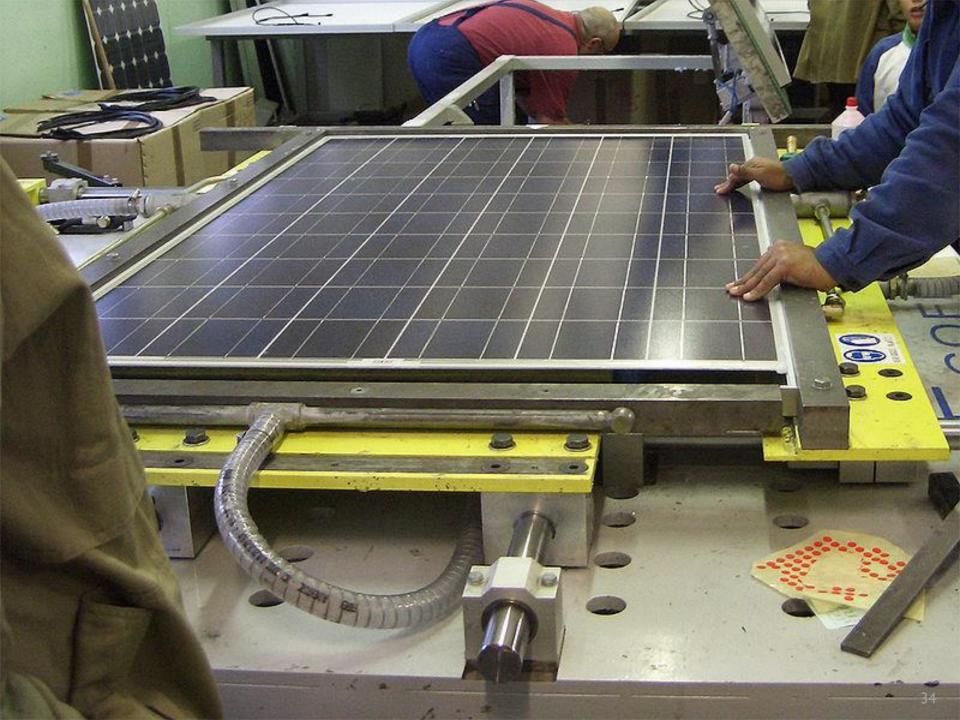
A typic al module has 36 cells in series



#### PV silicon module

- Packing density
- Interconnection PV cells
- Encapsulation
  - Good transmittance but UV absorbance
  - Rigidity to withstand mechanical loads
  - Protection from weather agents and humidity



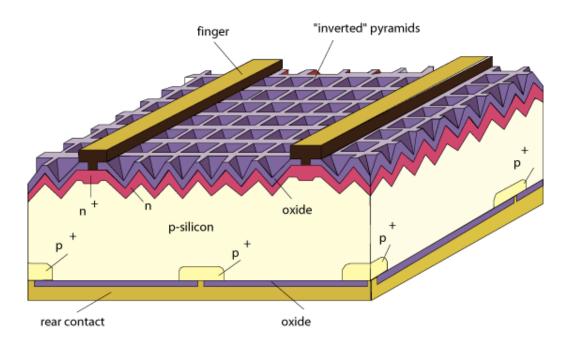


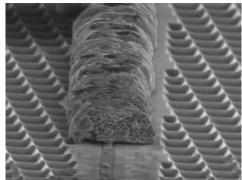


Is there a c-Si technology?

Is there a c-Si technology?

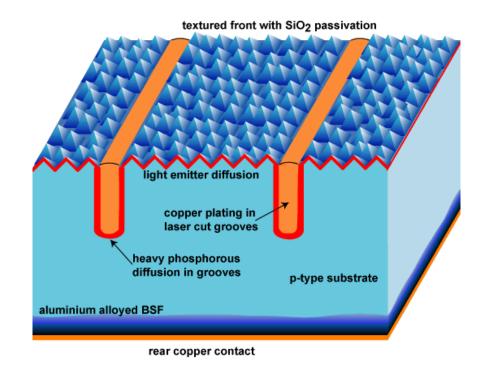
PERL solar cell

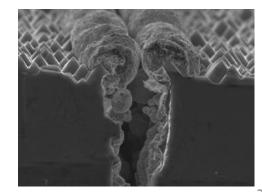




Is there a c-Si technology?

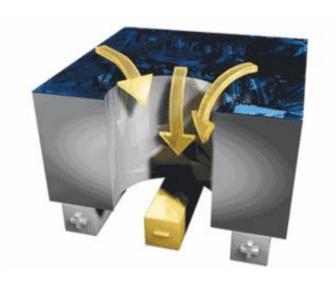
Buried contact solar cell

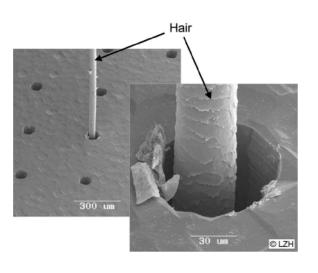




Is there a c-Si technology?

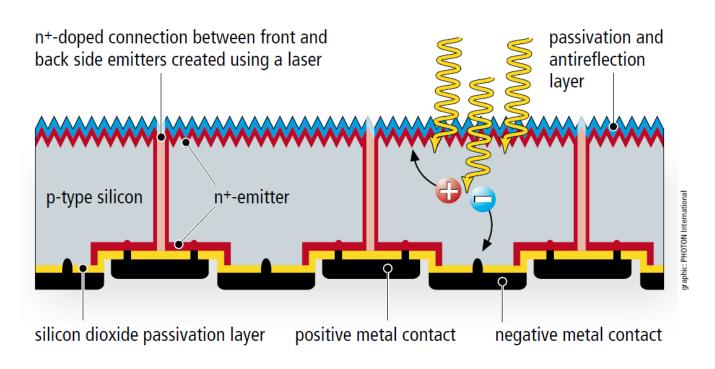
Rear interdigitated (RISE) solar cell





Is there a c-Si technology?

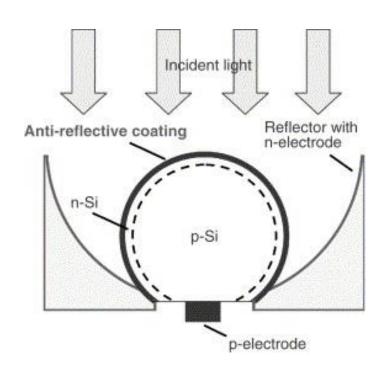
Rear interdigitated (RISE) solar cell

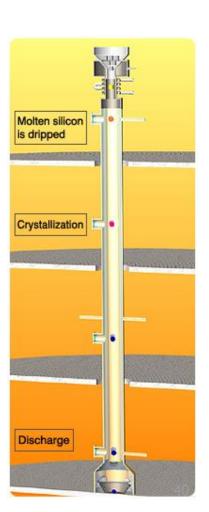


Is there a c-Si technology?

Spheral solar cell

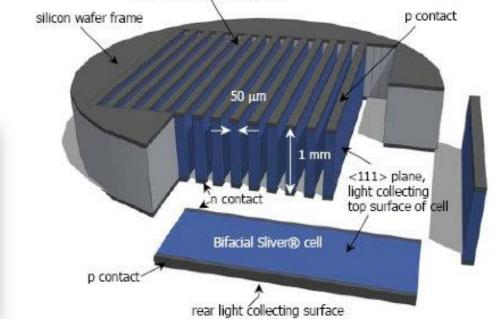






Is there a c-Si technology?

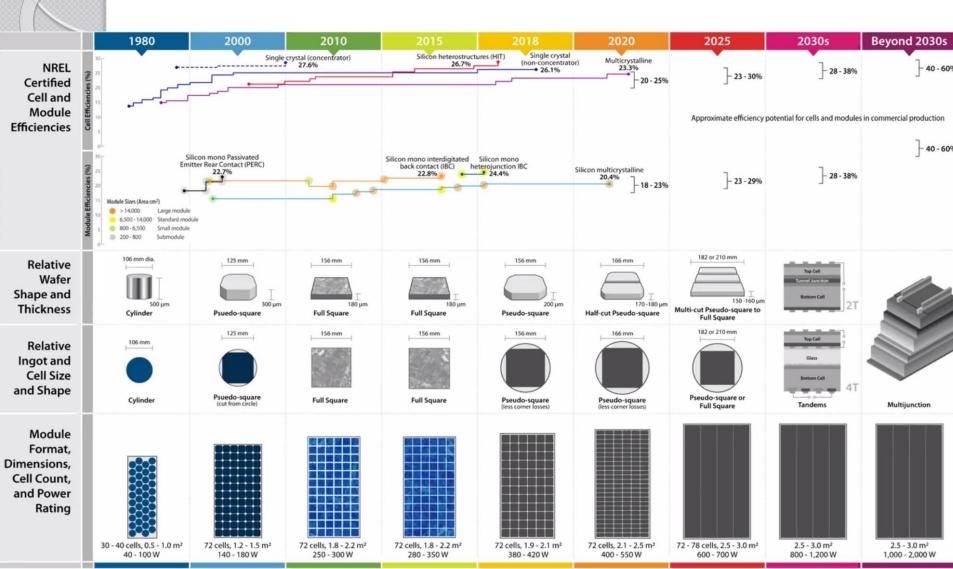
Sliver solar cell



individual Sliver® cells, micro machined

out of a p-type silicon wafer





#### Materials availability

- Silicon is very abundant...
- Silver paste for the contacts will be a material bottleneck
- Other (temporary) bottlenecks:
  - Module glass
  - Tedlar
  - EVA

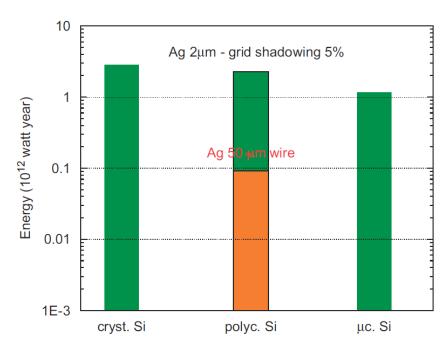
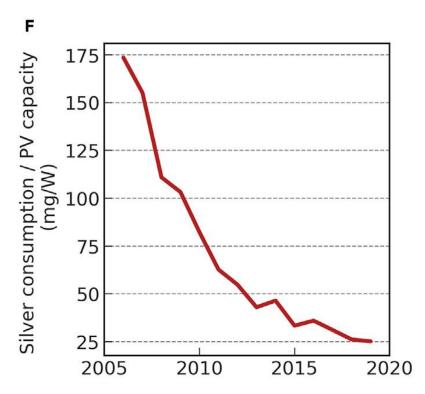


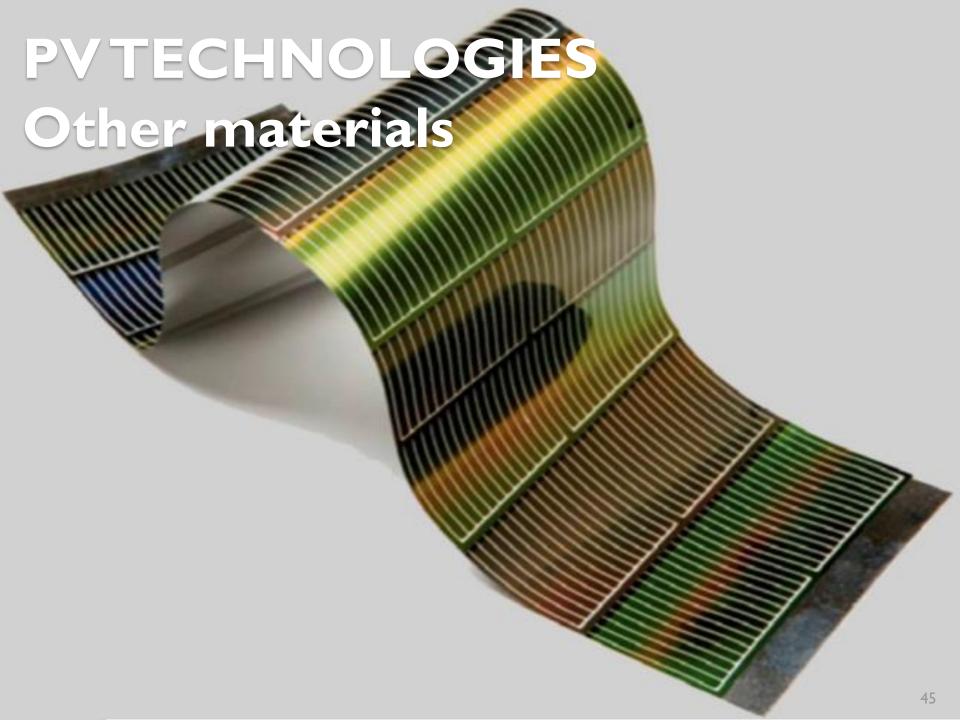
Fig. 3. Potential energy limits imposed by global silver (Ag) reserves for bulk-like silicon photovoltaic technologies. Calculations assume AM1.5 efficiencies of 24.7% (Ref. [8]) and 20.3% (Ref. [7]) for crystalline and large grain poly-crystalline solar cells. The orange shaded area represents limits reached using 50  $\mu$ m-thick Ag ribbons. The green shaded area represents limits estimated using a 2  $\mu$ m thick Ag electrodes and 5% grid shadowing.



#### Materials availability

- Silicon is very abundant...
- Silver paste for the contacts will be a material bottleneck
- Other (temporary) bottlenecks:
  - Module glass
  - Tedlar
  - EVA



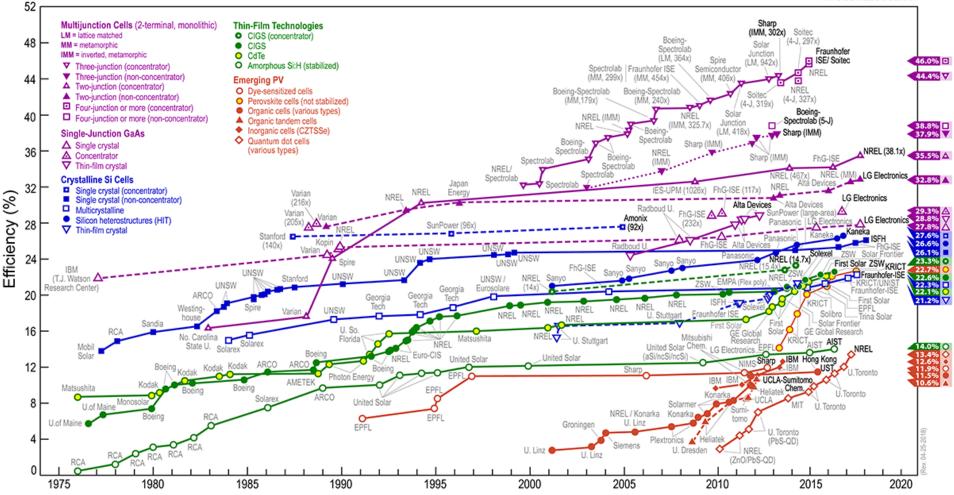




- Other concepts, materials & technologies
  - a-Si
  - CIGS
  - CdTe
- It's not only about efficiency (nor cost!)

#### **Best Research-Cell Efficiencies**



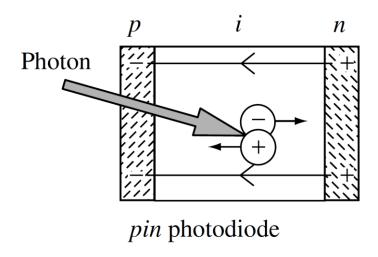




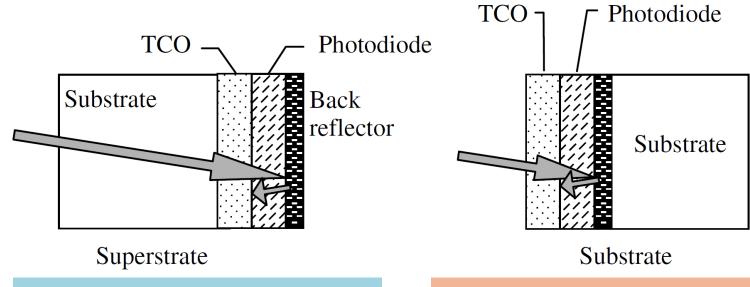
- Amorphous commonly applied to noncrystalline materials prepared by deposition from gases
- First working a-Si based solar cell: Carlson D, Wronski C, Appl. Phys. Lett. 28, 671 (1976)
- Cheaper deposition
- Hydrogenated amorphous silicon (a-Si:H)
  has higher absorption coefficient than
  crystalline silicon much thinner (< I μm)
  solar cells are possible</li>

### p-i-n configuration

- Electron-hole pairs are generated in the intrinsic 'thick' layer and
- Separated by the built electric field



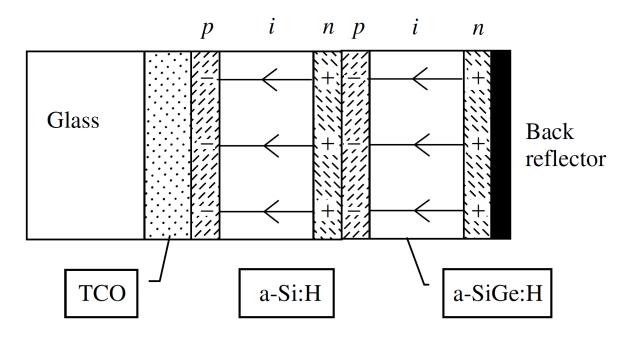
Very thin active layer ( $< I \mu m$ ) thus: requires substrate



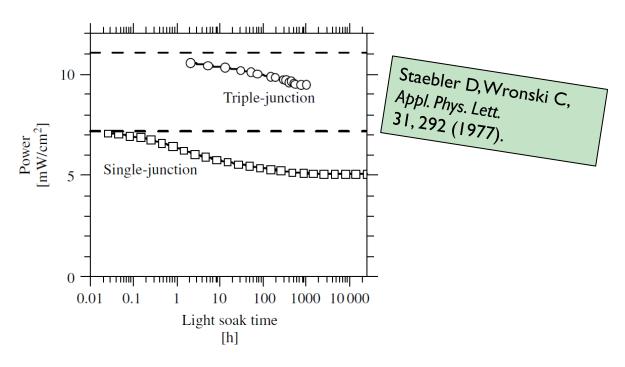
Substrate may be glass: useful for building **integrated** PV

Substrate may be foil: useful for **flexible** solar cells

To increase efficiency, more junctions (tandem configuration) may be added



Significant decline in their efficiency during their first few hundred hours of illumination: Staebler-Wronski effect



**Figure 12.5** The conversion efficiency in a-Si:H-based solar cells declines noticeably upon the first exposure to sunlight. The figure illustrates this decline under a solar simulator (100 mW/cm<sup>2</sup>) for a single-junction cell (260-nm i-layer thickness) and for a triple-junction module made at United Solar Systems Corp. [14, 15]; the dashed lines indicate the initial power measured for each device

**PECVD** - Plasma enhanced chemical vapour deposition (a.k.a. RF glow discharge deposition)

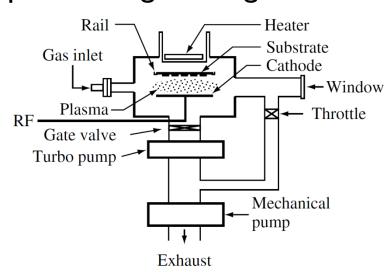
SiH4 + H2 into the chamber

RF is applied and generates plasma

plasma excites and decomposes the gas and generates

radicals and ions

 that will diffuse onto the heated substrate

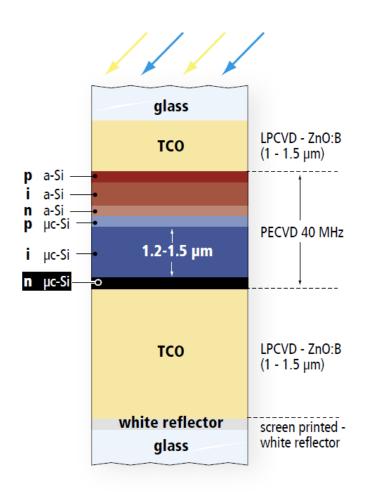


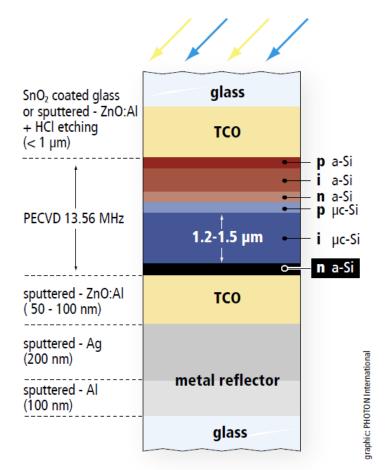
#### **Oerlikon**

based on process developed at the University of Neuchâtel

#### **Applied Materials**

based on process developed at Research Center Jülich (FZJ)







#### In summary:

- Low efficiency (for the same yield requires more area: module framing & encapsulation become relevant costs)
- Low cost (may be interesting if land availability is not an issue)
- Niche markets such as building integrated PV, consumer electronics (i.e. gadgets), flexible solar cells,...



- CdTe has a high absorption coefficient: thus very thin active layer
- Earliest paper on CdTe solar cell:
   Loferski J, J. Appl. Phys. 27, 777–784 (1956)
- Most 'popular' configuration: CdTe/CdS heterojunction (p-type CdTe and n-type CdS)

#### Letters to the Editor

PUBLICATION of brief reports of important discoveries in physics may be secured by addressing them to this department. The closing date for this department is five weeks prior to the date of issue. No proof will be sent to the authors. The Board of Editors does not hold itself responsible for the opinions expressed by the correspondents. Communications should not exceed 600 words in length and should be submitted in duplicate.

#### High-Voltage Photovoltaic Effect\*

L. Pensak

RCA Laboratories, Princeton, New Jersey (Received November 25, 1957)

VACUUM evaporated films of cadmium telluride have been prepared that show unusually high photovoltages across their ends. The effect is independent of the electrode material and the voltage is proportional to the length of the film. A value of one hundred volts/cm has been obtained in sunlight. Since the photovoltage of a single junction is limited by the band gap of the material (1.45 ev), it is concluded that the films consist of large numbers of junctions (or other photovoltaic elements) whose individual voltages add to produce the observed values. Photovoltages greater than band gap have been reported for films of PbS, 1,2 but with a maximum of 3 volts and only after some post-evaporation processing. No such processing is required for the CdTe films.

The presence of the effect depends on the angle,  $\theta$ , of deposition of the vapor onto the substrate as shown in Fig. 1. Lines of constant  $\theta$  are found to be equipotentials for photovoltage. No photovoltage exists in material deposited with  $\theta=0$ . The photovoltage increases rapidly with  $\theta$  up to about 10 degrees and then very slowly up to 60 degrees, above which no measurements were taken. A second requirement for the effect is that the substrate be held at a temperature between 100 and 250°C during deposition. The pressure during evaporation,  $\sim 10^{-5}$  mm, is maintained by an oil diffusion pump.

The rate of film formation is about 1000 A per minute. The films become photovoltaic when the thickness is sufficient to absorb some light, and the voltage increases to a maximum at approximately one micron. The effect occurs with Pyrex glass, fused quartz, and other substrate materials. The only requirement is that the substrate be more insulating than the films which, in the dark, have a resistance of the order of 10<sup>13</sup> ohms per square at room temperature.

The electrical properties of the films and their response to light and temperature are reported in a following letter. Optical transmission measurements show that the fundamental absorption edge is 8300 A, the expected value for CdTe. X-ray studies by J. G. White of this Laboratory are consistent with the view that the films consist of crystallites whose size is comparable with the film thickness ( $\sim 1 \mu$ ). The crystallite (111) planes have a preferred orientation parallel to the substrate, regardless of the angle of deposition.

Although the effect has been found in every film made, the magnitude has not been reproducible within a factor of 10. An explicit model for the mechanism of the effect has not yet been established. An effect of comparable magnitude has been found in single-crystal zinc sulfide by another group in this laboratory. Further studies of the effect in both materials are under way.

- \* This work was supported by the Evans Signal Corps Laboratories.
- <sup>1</sup> Starkiewicz, Sosnowski, and Simpson, Nature 158, 26 (1946).
  <sup>2</sup> Berlaga, Rusmach, and Strakhov, Zhur. Tekh. Fiz. 25, 1878 (1955).

#### Properties of Photovoltaic Films of CdTe†

B. Goldstein

RCA Laboratories, Princeton, New Jersey (Received November 25, 1957)

THIS letter describes some of the basic properties of a representative photovoltaic film of CdTe.<sup>1</sup> The film was deposited onto a Pyrex substrate: it was one-half cm long, one cm wide, and about one micron thick. The open-circuit voltages were measured with a

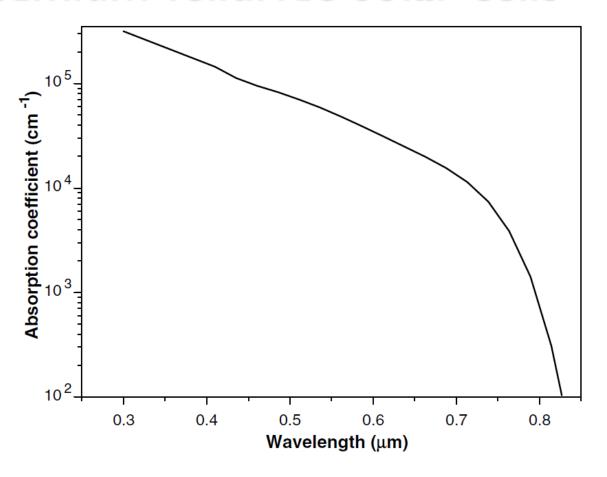
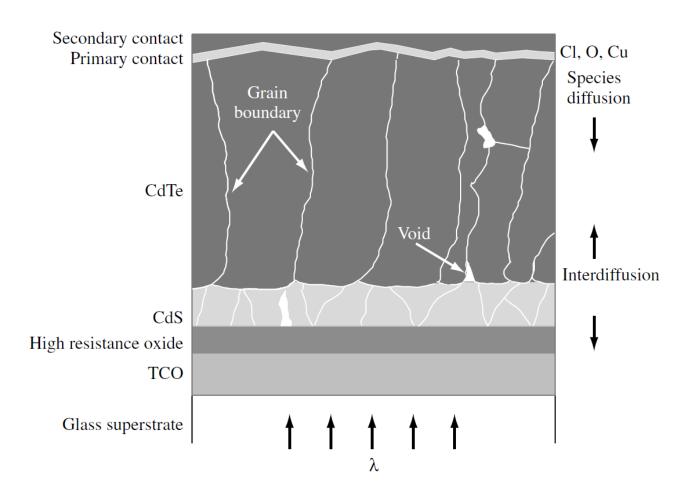
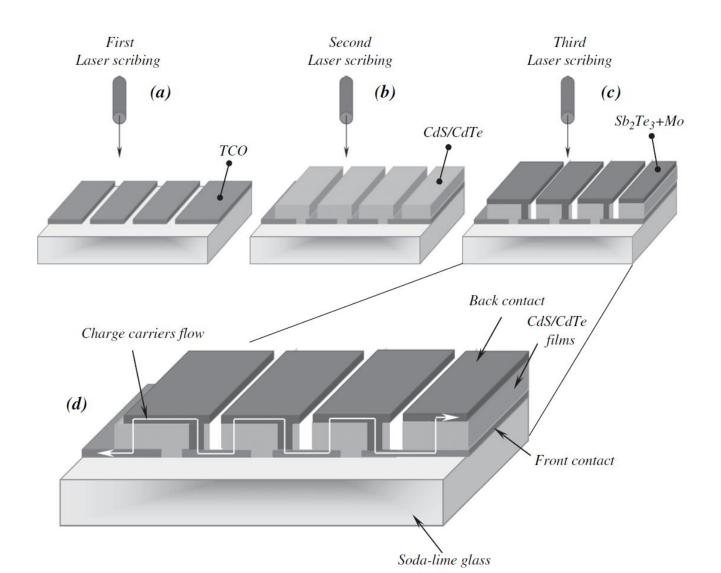


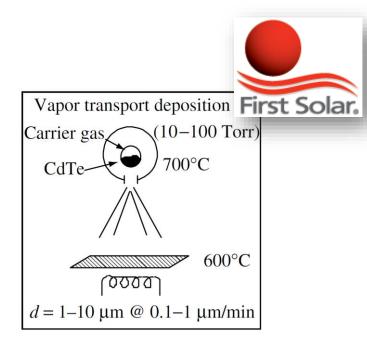
Fig. 5. CdTe absorption coefficient at room temperature.



**Figure 14.7** Basic CdTe solar cell structure. The polycrystalline nature of the CdS and CdTe layers are indicated schematically and are not to scale



- Top efficiencies:
  - Cell 16.7% (NREL);
  - Module 10.9% (BP Solarex);
  - Best seller: First Solar



#### Main issues:

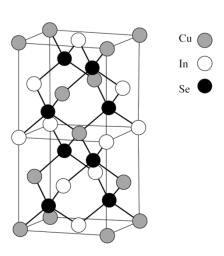
- Cheapest technology in the market (<I€/Wp)</li>
- 'Limited' efficiency
- Reliability (lifetime)
- Materials!!
  - Toxic Cd
  - Rare Te
- Window of opportunity taken!

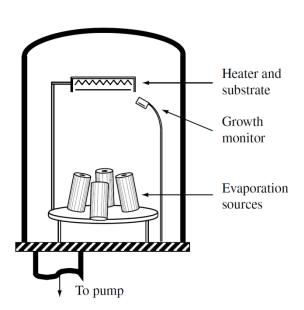


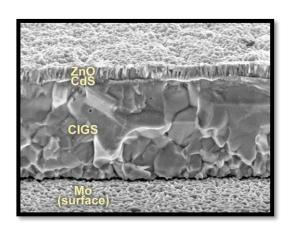
- Synthesis and characterization were first reported by Hahn H et al., Z. Anorg. Allg. Chem. 271, 153–170 (1953)
- High absorption coefficient: thin film
- Like all thin films: potential for cheap manufacturing for fabrication of monolithically interconnected modules
- Potential for relatively high efficiency: 19.4% (cell) and 13.5% (module)

# PV TECHNOLOGIES Cu(InGa)Se<sub>2</sub> solar cells

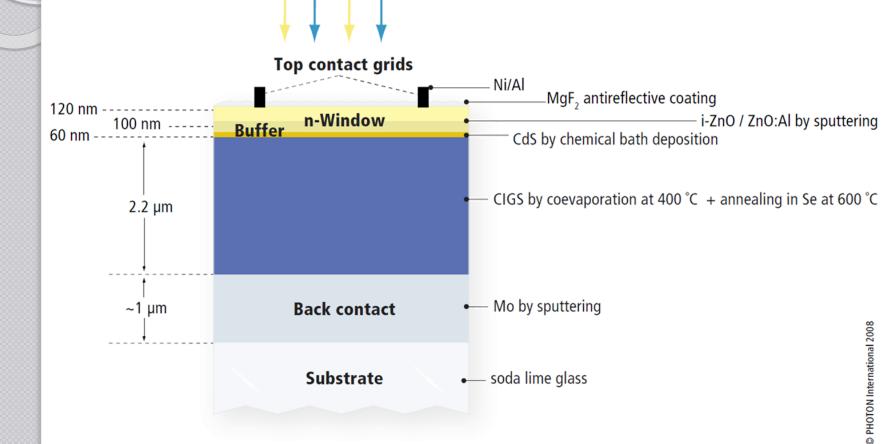
- P-type: Cu(InGa)Se<sub>2</sub>
- N-type: CdS







# PV TECHNOLOGIES Cu(InGa)Se<sub>2</sub> solar cells



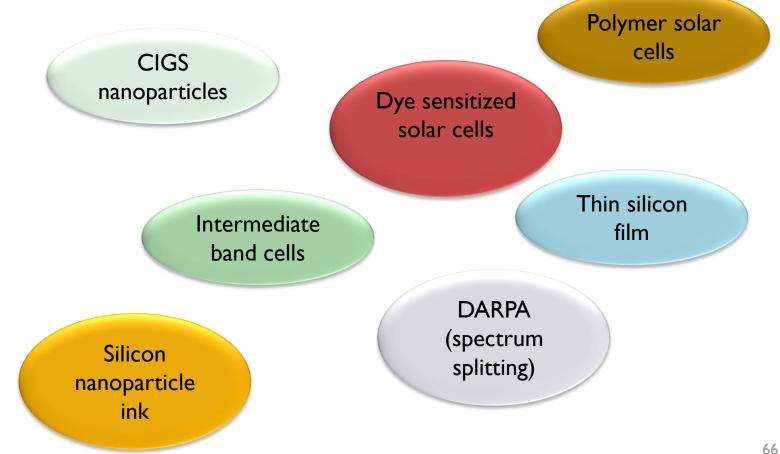
# PV TECHNOLOGIES Cu(InGa)Se<sub>2</sub> solar cells

Other different CIGS concepts...

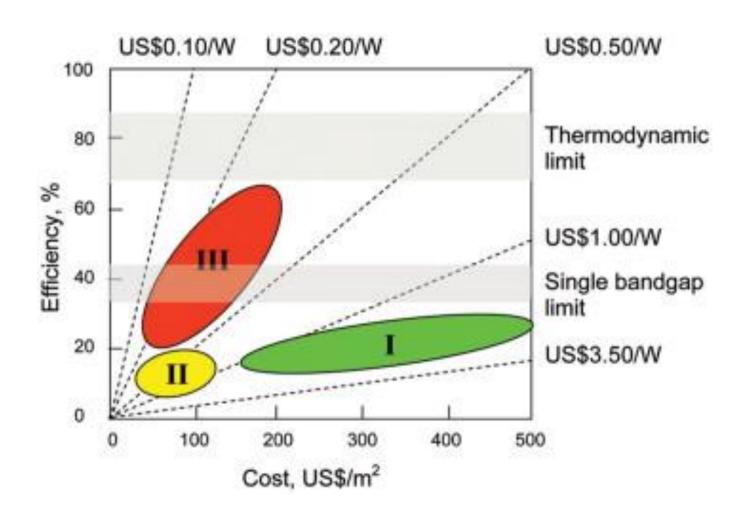


### **PV TECHNOLOGIES** Other technologies

Many other different concepts...

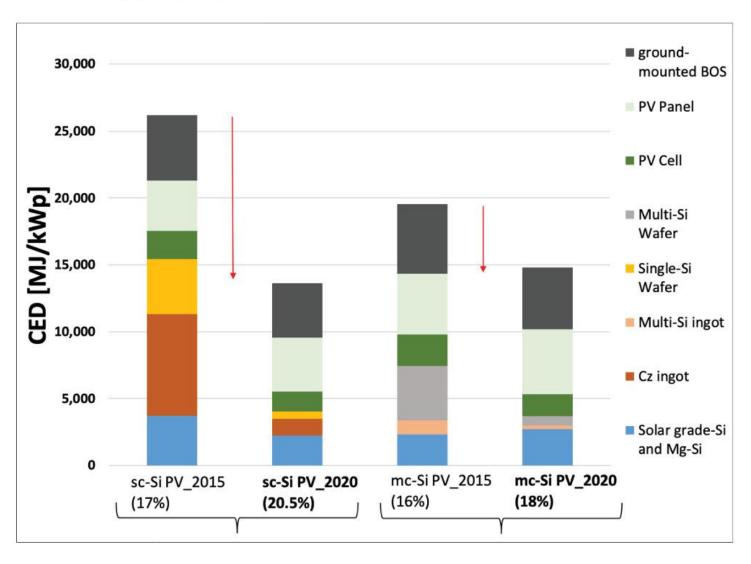


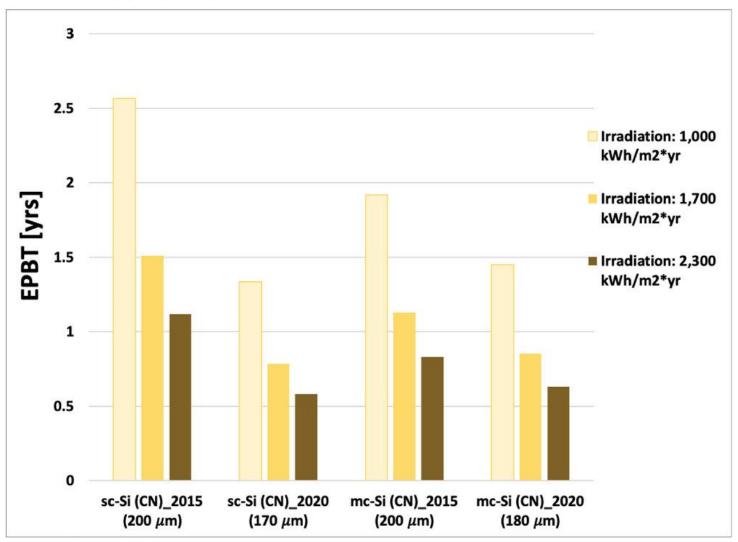
## PV TECHNOLOGIES Other technologies

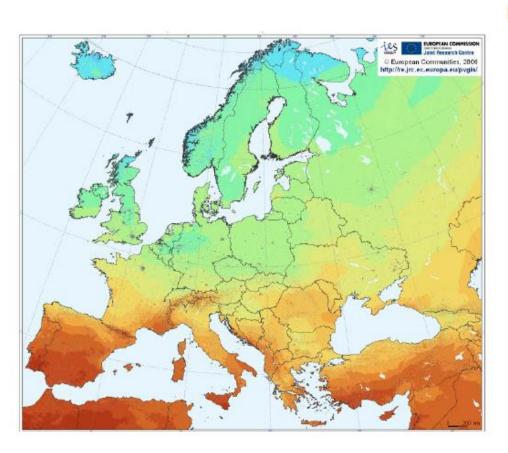


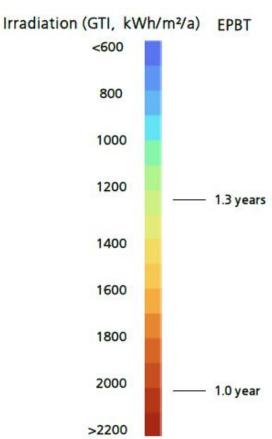
# PV TECHNOLOGIES Comparing different technologies



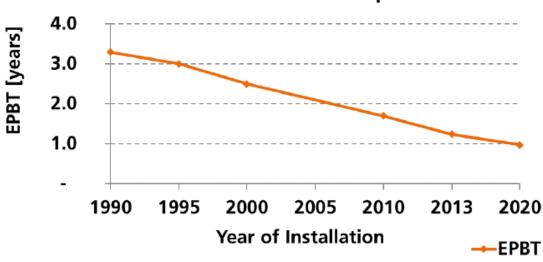








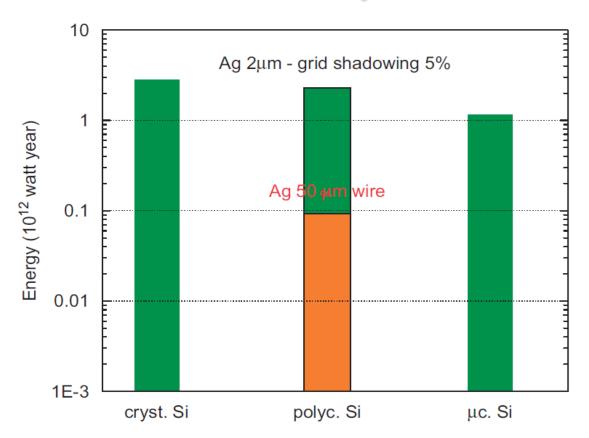
EPBT of crystalline PV rooftop systems installed in Southern Europe\*



\*Irradiation: 1700 kWh/m²/a at an optimized tilt angle

 $energy yield = \frac{operational lifetime}{energy payback time}$ 

## PV TECHNOLOGIES Materials availability



Potential energy limits imposed by global silver (Ag) reserves for bulk-like silicon photovoltaic technologies. The orange shaded area represents limits reached using 50 mm-thick Ag ribbons. The green shaded area represents limits estimated using a 2 mm thick Ag electrodes and 5% grid shadowing.

## PV TECHNOLOGIES Materials availability

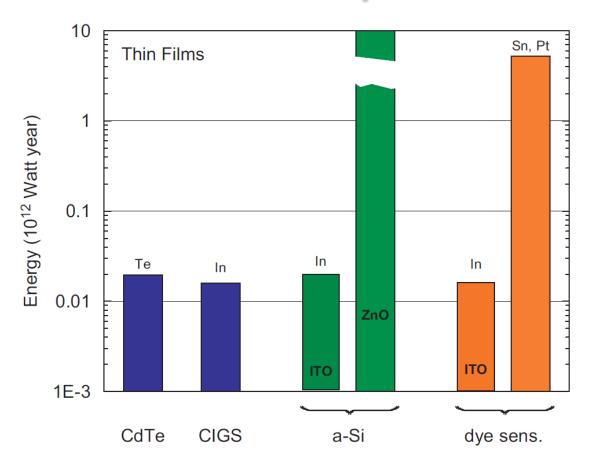


Fig. 4. Potential energy limits imposed for four different thin film photovoltaic technologies.

## PV TECHNOLOGIES Materials availability

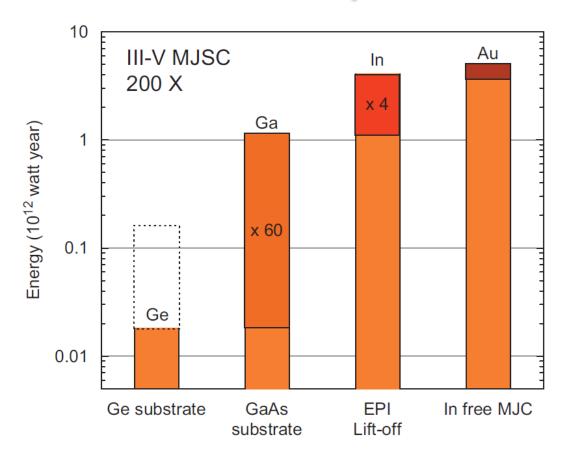


Fig. 5. Potential energy limits imposed to III–V multi-junction cells (200 sun concentrations). The third and fourth columns show the extrapolated potential of this technology if lift-off/cell exfoliation techniques are adopted.



#### Considering all these factors...

- Silicon technologies are to dominate the market in the foreseeable future
- Opportunities for other technologies with industrial scale, in particular CdTe (e.g. First Solar)
- Niche markets are breeding ground for other 'new' technologies (thin films in BIPV or flexible applications, concentration for large solar power plants, etc)